

**AMENDMENTS TO THE CLAIMS:**

Please cancel claims 1, 2, 13, 15, 23, and 24 without prejudice or disclaimer of their subject matter. This listing of claims will replace all prior versions and listings of claims in the application:

**LISTING OF CLAIMS:**

1. - 15. (Canceled)

16. (Previously Presented) A semiconductor device comprising:

a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;

an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film;

an Al film formed on the Ta film and used as a pad, the Al film having a horizontally extending portion under which the Cu film is not formed; and

a conductive connection member connected to the Al film at the horizontally extending portion.

17. (Previously Presented) The semiconductor device according to claim 16, wherein the intermediate layer has a first portion which contacts the Cu film and a second portion which does not contact the Cu film, and an insulating film contacts the second portion.

18. (Previously Presented) The semiconductor device according to claim 16, wherein the intermediate layer has a portion corresponding to the extending portion.

19. (Previously Presented) The semiconductor device according to claim 16, wherein the conductive connection member includes a bonding wire.

20. (Previously Presented) The semiconductor device according to claim 16, wherein a thickness of the Ta film is 5 nm or less.

21. (Previously Presented) The semiconductor device according to claim 16, wherein a thickness of the TaN film is 20 nm or more.

22. (Previously Presented) The semiconductor device according to claim 16, wherein a thickness of the TaN film is 40 nm or more.

23. (Canceled)

24. (Canceled)

25. (Previously Presented) The semiconductor device according to claim 16, wherein no conductive connection member is connected to that portion of the Al film under which the Cu film is formed.

26. (Previously Presented) The semiconductor device according to claim 16, wherein the Al film has a plurality of vertically extending portions extending toward the Cu film, and wherein the intermediate layer has a plurality of portions provided between the vertically extending portions and the Cu film.

27. (Previously Presented) The semiconductor device according to claim 26, further comprising an insulating film surrounding each of the vertically extending portions.